

AMENDMENTS TO THE CLAIMS

1. (Previously Presented) A semiconductor device, comprising:
an insulating layer;
an interconnect line embedded in said insulating layer;
a circuit element mounted on said insulating layer;
a packaging layer formed to cover said circuit element; and
an electroconductive shielding film formed to cover said packaging layer,
wherein:
said interconnect line is electrically coupled to said shielding film;
said shielding film is in contact with said packaging layer; and
said shielding film and said packaging layer are formed of materials having a similar
coefficient of linear expansion.
 2. (Original) The semiconductor device according to claim 1, further comprising a
protective film formed to cover said shielding film, said protective film comprising a material
having higher corrosion resistance than that of a material that is included in said shielding film.
- Claims 3-9 (Canceled)
10. (New) The semiconductor device according to claim 1, wherein the interconnect
line and the shielding film are formed of the same electro conductive material.